

Substitute for form 1449A/PTO		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>		Application Number	10/606,176
(use as many sheets as necessary)		Filing Date	June 25, 2003
		First Named Inventor	Yoshihide Nakamura
		Art Unit	2811
		Examiner Name	Ori Nadav
		Attorney Docket Number	09792909-5625
Sheet	of		

## U.S. PATENT DOCUMENTS

## FOREIGN PATENT DOCUMENTS

Examiner Signature	ON	Date Considered	2/20/07
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Substitute for form 1449B/PTO				<b>Complete if Known</b>	
				Application Number	10/606,176
				Filing Date	June 25, 2003
				First Named Inventor	Yoshihide Nakamura
				Art Unit	2811
				Examiner Name	Ori Nadav
Sheet		of		Attorney Docket Number	09792909-5625

<b>OTHER ITEMS – NON PATENT LITERATURE DOCUMENTS</b>				
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T <sup>2</sup>
ON		<i>"InGaN Multi-Quantum-Well-Structure Laser Diodes with Cleaved Mirror Cavity Facets,"</i> Jpn. J. Appl. Phys., Vol. 35, 1996, pp. L217-L220		
		<i>"Blue InGaN-Based Laser Diodes with an Emission Wavelength of 450nm"</i> Appl. Phys. Lett., Vol. 76, 2000, pp. 22-24		
		<i>"First III-V-Nitride-Based Violet Laser Diodes"</i> J. Crystal Growth, Vol. 170, 1997, pp. 11-15		
		<i>"High-Power, Long-Lifetime InGaN/GaN/AlGaN-Based Laser Diodes Grown on Pure GaN Substrates."</i> Jpn. J. Appl. Phys., Vol. 35, 1998, pp. L309-L312		
		<i>"InGaN/GaN/AlGaN-Based Laser Diodes Grown on Epitaxially Laterally Overgrown GaN,"</i> J. Mater. Res., Vol. 14, No. 7, 1999, pp. 2716-2731		
ON		<i>"InGaN/GaN/AlGaN-Based Laser Diodes with Modulation-Doped Strained-Layer Superlattices,"</i> Jpn. J. Appl. Phys., Vol. 36, 1997, pp. 1568-1571		
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